

Application No. **09/500,288**

GaN substrate with crack prevention and special grow method to reduce compressive strain and thermal relief

East Search

Search	L. No.	Hits	Text Search			Data Bases
BRS	L1	270769	(led (light adj emitting adj device))		6/21/01 11:43	USPAT: EPO: JPO: Derwent: IBM TDB
BRS	L2	1152	1 and gan		6/21/01 11:43	USPAT: EPO: JPO: Derwent: IBM TDB
BRS	L3	4	2 and (crack adj prevention)		6/21/01 11:44	USPAT: EPO: JPO: Derwent: IBM TDB
BRS	L4	15	2 and (compressive adj strain)		6/21/01 11:53	USPAT: EPO: JPO: Derwent: IBM TDB
BRS	L2	49	1 and (concave convex)		6/21/01 13:03	USPAT: EPO: JPO: Derwent: IBM TDB
BRS	L7	77	((led (light adj emitting adj device))) and ((gan (gallium adj nitride)) adj substrate)		6/21/01 13:59	USPAT: EPO: JPO: Derwent: IBM TDB
BRS	L8	30	7 and (single adj crystal)		6/21/01 13:59	USPAT: EPO: JPO: Derwent: IBM TDB
BRS	L9	5	8 and compressive adj strain		6/21/01 13:59	USPAT: EPO: JPO: Derwent: IBM TDB

Search Result

USPAT	Date	Page	Title	Cl/Sub	Cl/Sub	Inventor
US 6153010 A	20001128	35	Method of growing nitride semiconductors, nitride semiconductor substrate and nitride semiconductor device	117/95	117/106 ; 117/952 ; 117/97	Kiyoku, Hiroyuki , et al.
US 5825796 A	19981020	32	Extended wavelength strained layer lasers having strain compensated layers	372/45	257/17 ; 257/18 ; 257/190 ; 257/94 ; 372/46	Jewell, Jack L. , et al.
US 6091083 A	20000718	26	Gallium nitride type compound semiconductor light-emitting device having buffer layer with non-flat surface	257/79	257/190 ; 257/196 ; 257/201 ; 257/615 ; 257/618 ; 257/622 ; 257/623 ; 257/76 ; 257/97 ; 372/45 ; 372/46	Hata, Toshio , et al.
US 6057878 A	20000502	36	Three-dimensional picture image display apparatus	348/56	348/51	Ogiwara, Akifumi , et al.
US 5838854 A	19981117	50	Integrated optical control element and a method for fabricating the same and optical integrated circuit element and optical integrated circuit device using the same	385/50	359/124	Taneya, Mototaka , et al.
US 5787104 A	19980728	44	Semiconductor light emitting element and method for fabricating the same	372/43	372/45	Kamiyama, Satoshi , et al.
US 20010002048 A1		26	Light-emitting device using group III nitride group compound semiconductor			Koike, Masayoshi , Yamakazi, Shiro , et al.
US 6072197 A	20000606	42	Semiconductor light emitting device with an active layer made of semiconductor having uniaxial anisotropy	257/103	257/627 ; 257/628 ; 257/94 ; 257/98	Horino, Kazuhiko , et al.
US 5689123 A	19971118	21	III-V arsenide-nitride semiconductor materials and devices	257/190	257/18 ; 257/184 ; 257/201 ; 257/22	Major, Jo S. , et al.

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Fast Search				6/21/01	
Search	L No.	Hits	Text Search		Data Bases
BRS	L7	1500	((led (light adj emitting adj device))) and (gan (gallium adj nitride))	6/21/01 14:58	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L8	292	7 and single adj crystal	6/21/01 14:58	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L9	8	8 and compressive adj strain	6/21/01 14:58	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L10	41	8 and (coefficient near (thermal adj expansion))	6/21/01 14:59	USPAT; EPO; JPO; Derwent; IBM TDB
BRS	L11	1	10 and lateral adj growth	6/21/01 15:00	USPAT; EPO; JPO; Derwent; IBM TDB

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